

SEMICONDUCTOR DEVICE AND METHOD OF PRODUCING SAME

ABSTRACT OF THE DISCLOSURE

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A semiconductor device, able to be produced while suppressing the occurrence of mesa shaped abnormalities without restriction as to the pattern layout, the type of etchant used, etc., provided with a semiconductor mesa
10 portion including a stack of a collector layer, a base layer, and an emitter layer on a substrate and functioning as an active region of a bipolar transistor, a base contact pad mesa portion separated from this by a predetermined distance and having a height the same as
15 the top surface of the base layer, and a conductor layer integrally formed with a base electrode connected to the base layer, a base contact pad electrode formed on the base contact pad mesa portion in a region other than near the edges of the top surface of the base contact pad mesa
20 portion, and an interconnect connecting these, and a method of producing the same.